

NCE N-Channel Super Trench II Power MOSFET

Description

The series of devices uses **Super Trench II** technology that is uniquely optimized to provide the most efficient high frequency switching performance. Both conduction and switching power losses are minimized due to an extremely low combination of $R_{DS(ON)}$ and Q_g . This device is ideal for high-frequency switching and synchronous rectification.

Application

- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

General Features

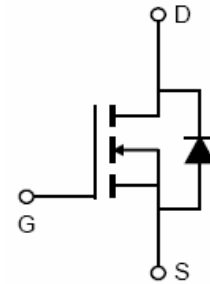
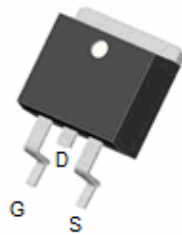
- $V_{DS} = 100V, I_D = 160A$
 $R_{DS(ON)} = 2.9m\Omega$, typical (TO-220) @ $V_{GS} = 10V$
 $R_{DS(ON)} = 2.7m\Omega$, typical (TO-263) @ $V_{GS} = 10V$
- Excellent gate charge x $R_{DS(on)}$ product(FOM)
- Very low on-resistance $R_{DS(on)}$
- 175 °C operating temperature
- Pb-free lead plating

100% UIS TESTED!
100% ΔVds TESTED!

TO-220



TO-263



Schematic Diagram

Package Marking and Ordering Information

| Device Marking | Device | Device Package | Reel Size | Tape width | Quantity |
|----------------|-------------|----------------|-----------|------------|----------|
| NCEP033N10 | NCEP033N10 | TO-220 | - | - | - |
| NCEP033N10D | NCEP033N10D | TO-263 | - | - | - |

Absolute Maximum Ratings ($T_C = 25^\circ C$ unless otherwise noted)

| Parameter | Symbol | Limit | Unit |
|---|--------------------|------------|------|
| Drain-Source Voltage | V_{DS} | 100 | V |
| Gate-Source Voltage | V_{GS} | ± 20 | V |
| Drain Current-Continuous | I_D | 160 | A |
| Drain Current-Continuous($T_C = 100^\circ C$) | $I_D(100^\circ C)$ | 120 | A |
| Pulsed Drain Current | I_{DM} | 640 | A |
| Maximum Power Dissipation | P_D | 245 | W |
| Derating factor | | 1.63 | W/°C |
| Single pulse avalanche energy ^(Note 5) | E_{AS} | 1345 | mJ |
| Operating Junction and Storage Temperature Range | T_J, T_{STG} | -55 To 175 | °C |

Thermal Characteristic

| | | | |
|--|-----------------|------|----------------------|
| Thermal Resistance, Junction-to-Case ^(Note 2) | $R_{\theta JC}$ | 0.61 | $^{\circ}\text{C/W}$ |
|--|-----------------|------|----------------------|

Electrical Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

| Parameter | Symbol | Condition | Min | Typ | Max | Unit | |
|--|--------------|---|--------|--------|-----------|---------|------------|
| Off Characteristics | | | | | | | |
| Drain-Source Breakdown Voltage | BV_{DSS} | $V_{GS}=0V, I_D=250\mu A$ | 100 | | - | V | |
| Zero Gate Voltage Drain Current | I_{DSS} | $V_{DS}=100V, V_{GS}=0V$ | - | - | 1 | μA | |
| Gate-Body Leakage Current | I_{GSS} | $V_{GS}=\pm 20V, V_{DS}=0V$ | - | - | ± 100 | nA | |
| On Characteristics ^(Note 3) | | | | | | | |
| Gate Threshold Voltage | $V_{GS(th)}$ | $V_{DS}=V_{GS}, I_D=250\mu A$ | 2.0 | 3.0 | 4.0 | V | |
| Drain-Source On-State Resistance | $R_{DS(on)}$ | $V_{GS}=10V, I_D=80A$ | TO-220 | - | 2.9 | 3.3 | m Ω |
| | | | TO-263 | | 2.7 | 3.3 | m Ω |
| Forward Transconductance | g_{FS} | $V_{DS}=5V, I_D=80A$ | 85 | - | - | S | |
| Dynamic Characteristics ^(Note 4) | | | | | | | |
| Input Capacitance | C_{iss} | $V_{DS}=50V, V_{GS}=0V,$ $F=1.0MHz$ | - | 7810.5 | - | PF | |
| Output Capacitance | C_{oss} | | - | 887.3 | - | PF | |
| Reverse Transfer Capacitance | C_{rss} | | - | 30 | - | PF | |
| Switching Characteristics ^(Note 4) | | | | | | | |
| Turn-on Delay Time | $t_{d(on)}$ | $V_{DD}=50V, I_D=80A$ $V_{GS}=10V, R_G=1.6\Omega$ | - | 25 | - | nS | |
| Turn-on Rise Time | t_r | | - | 15 | - | nS | |
| Turn-Off Delay Time | $t_{d(off)}$ | | - | 52 | - | nS | |
| Turn-Off Fall Time | t_f | | - | 17 | - | nS | |
| Total Gate Charge | Q_g | $V_{DS}=50V, I_D=80A,$ $V_{GS}=10V$ | - | 127.7 | - | nC | |
| Gate-Source Charge | Q_{gs} | | - | 41.8 | | nC | |
| Gate-Drain Charge | Q_{gd} | | - | 35.5 | | nC | |
| Drain-Source Diode Characteristics | | | | | | | |
| Diode Forward Voltage ^(Note 3) | V_{SD} | $V_{GS}=0V, I_S=80A$ | - | | 1.2 | V | |
| Diode Forward Current ^(Note 2) | I_S | | - | - | 160 | A | |
| Reverse Recovery Time | t_{rr} | $T_J = 25^{\circ}\text{C}, I_F = 80A$ $di/dt = 100A/\mu s$ ^(Note 3) | - | 74 | - | nS | |
| Reverse Recovery Charge | Q_{rr} | | - | 164 | - | nC | |

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.
4. Guaranteed by design, not subject to production
5. EAS condition : $T_J=25^{\circ}\text{C}, V_{DD}=50V, V_G=10V, L=0.5mH, R_g=25\Omega$

Typical Electrical and Thermal Characteristics

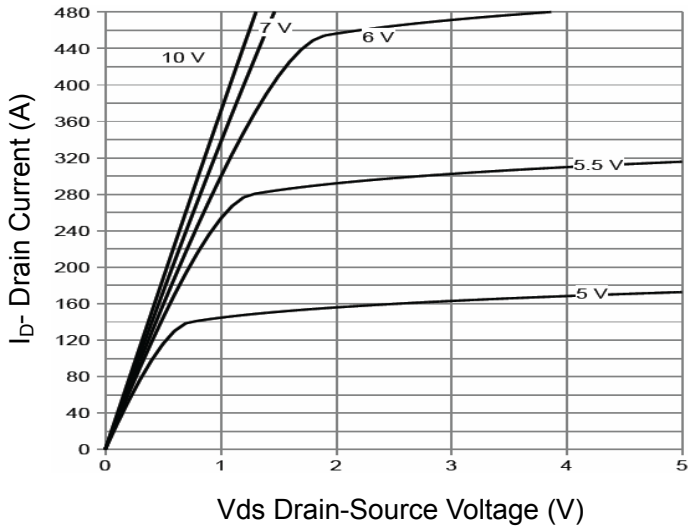


Figure 1 Output Characteristics

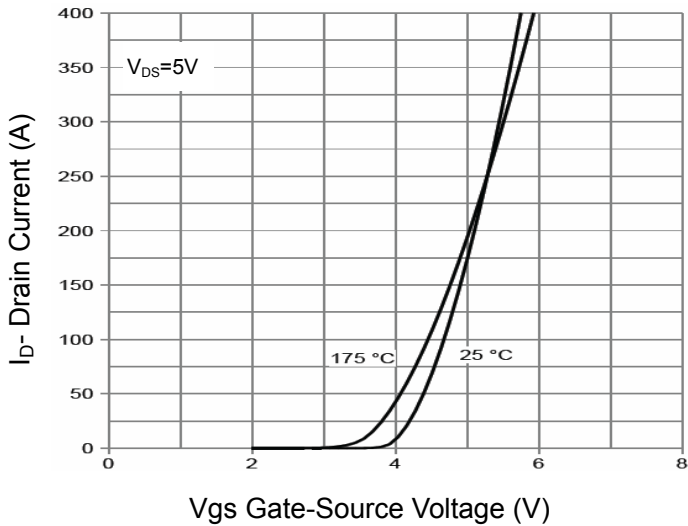


Figure 2 Transfer Characteristics

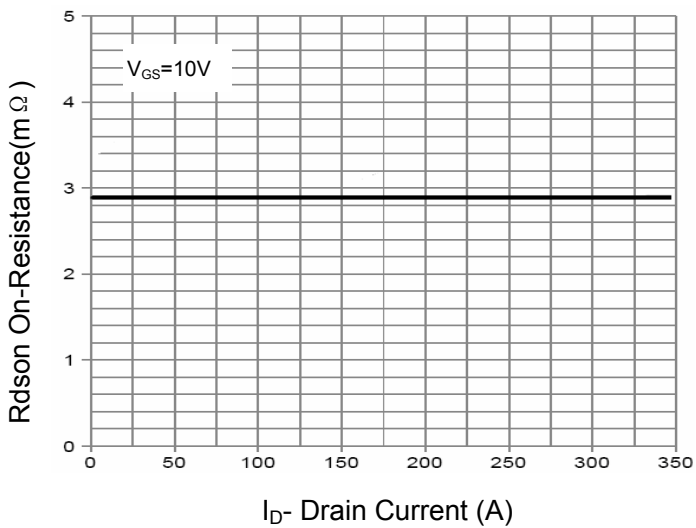


Figure 3 Rdson- Drain Current

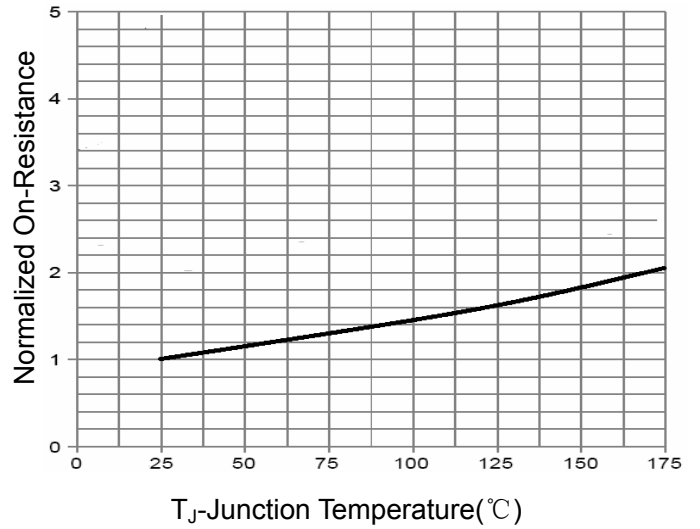


Figure 4 Rdson-Junction Temperature

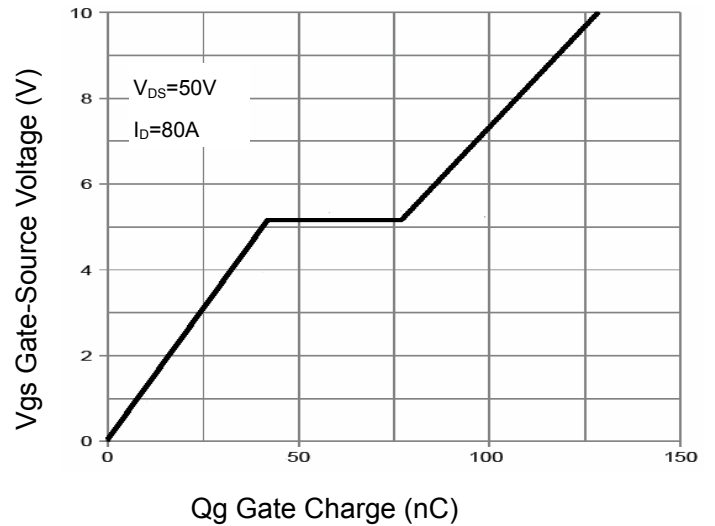


Figure 5 Gate Charge

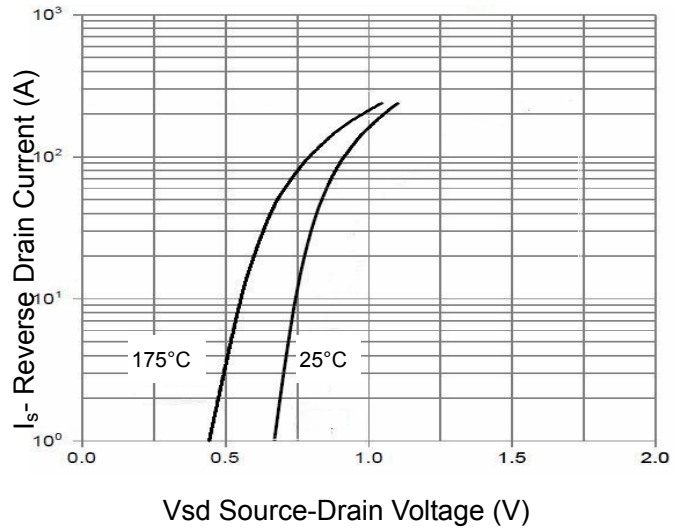
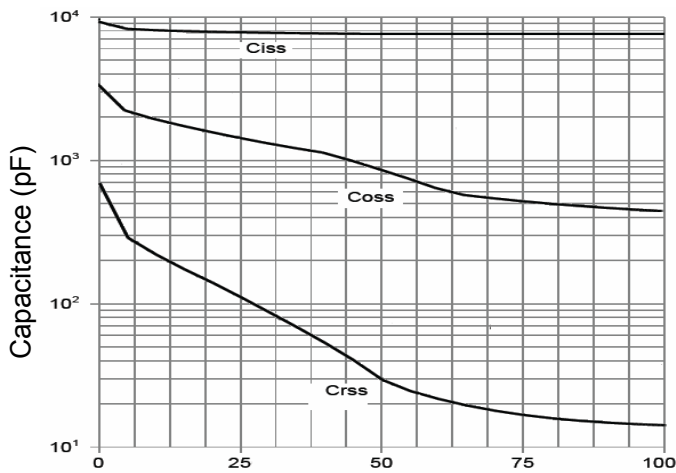


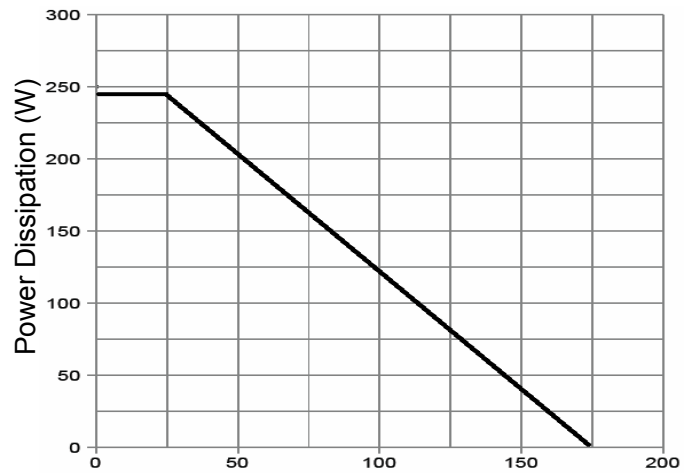
Figure 6 Source- Drain Diode Forward

$V_{GS}=10V$

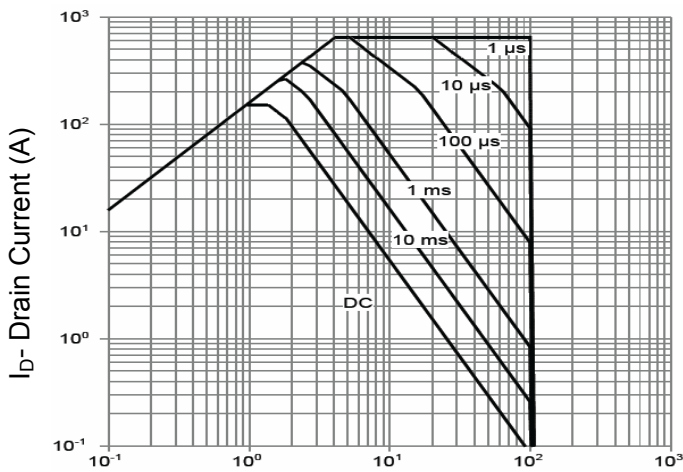
$I_D=80A$



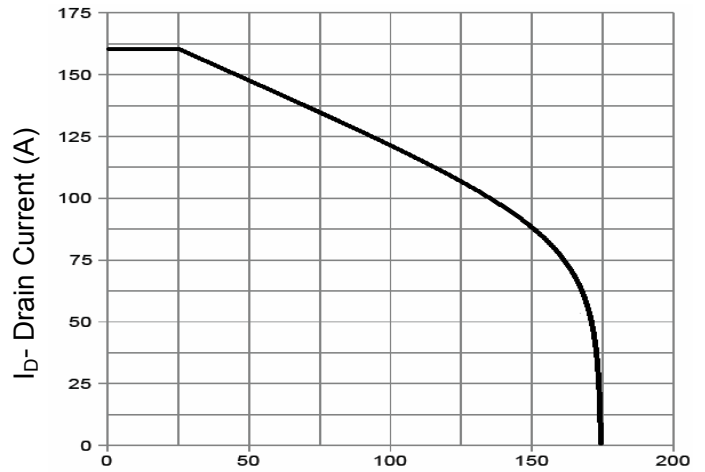
Vds Drain-Source Voltage (V)
Figure 7 Capacitance vs Vds



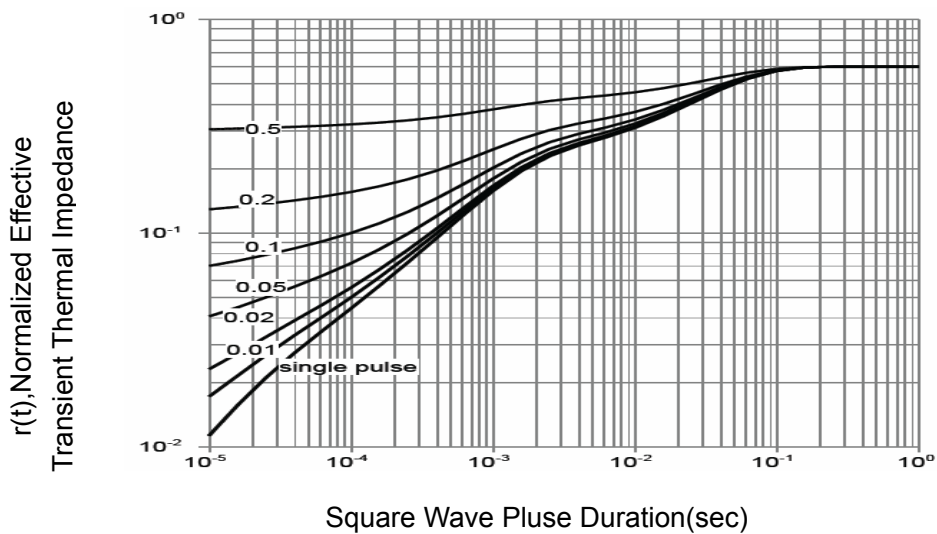
T_C-Case Temperature(°C)
Figure 9 Power De-rating



Vds Drain-Source Voltage (V)
Figure 8 Safe Operation Area



T_C-Case Temperature (°C)
Figure 10 Current De-rating



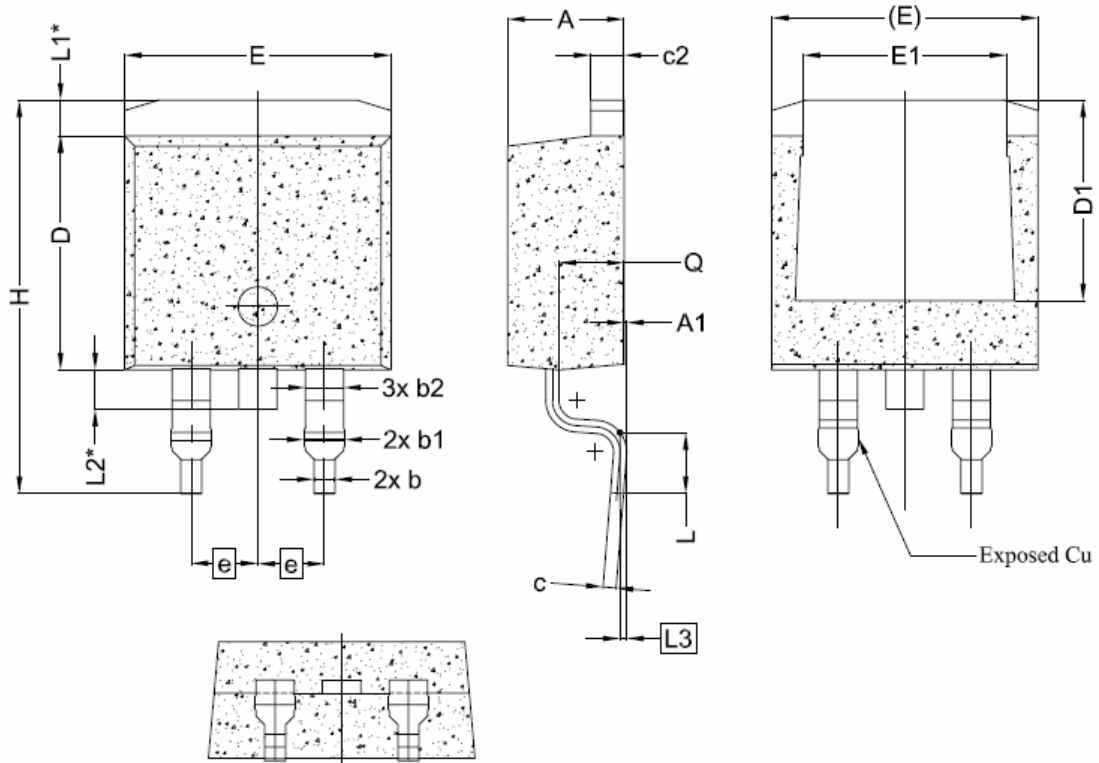
Square Wave Pluse Duration(sec)
Figure 11 Normalized Maximum Transient Thermal Impedance

TO-220-3L Package Information



| Symbol | Dimensions In Millimeters | | Dimensions In Inches | |
|--------|---------------------------|--------|----------------------|-------|
| | Min. | Max. | Min. | Max. |
| A | 4.400 | 4.600 | 0.173 | 0.181 |
| A1 | 2.250 | 2.550 | 0.089 | 0.100 |
| b | 0.710 | 0.910 | 0.028 | 0.036 |
| b1 | 1.170 | 1.370 | 0.046 | 0.054 |
| c | 0.330 | 0.650 | 0.013 | 0.026 |
| c1 | 1.200 | 1.400 | 0.047 | 0.055 |
| D | 9.910 | 10.250 | 0.390 | 0.404 |
| E | 8.9500 | 9.750 | 0.352 | 0.384 |
| E1 | 12.650 | 12.950 | 0.498 | 0.510 |
| e | 2.540 TYP. | | 0.100 TYP. | |
| e1 | 4.980 | 5.180 | 0.196 | 0.204 |
| F | 2.650 | 2.950 | 0.104 | 0.116 |
| H | 7.900 | 8.100 | 0.311 | 0.319 |
| h | 0.000 | 0.300 | 0.000 | 0.012 |
| L | 12.900 | 13.400 | 0.508 | 0.528 |
| L1 | 2.850 | 3.250 | 0.112 | 0.128 |
| V | 6.900 REF. | | 0.276 REF. | |
| Φ | 3.400 | 3.800 | 0.134 | 0.150 |

TO-263-2L Package Information



| Symbol | Dimensions In Millimeters | | |
|--------|---------------------------|-------|-------|
| | Min. | Nom. | Max. |
| A | 4.24 | 4.44 | 4.64 |
| A1 | 0.00 | 0.10 | 0.25 |
| b | 0.70 | 0.80 | 0.90 |
| b1 | 1.20 | 1.55 | 1.75 |
| b2 | 1.20 | 1.45 | 1.70 |
| c | 0.40 | 0.50 | 0.60 |
| c2 | 1.15 | 1.27 | 1.40 |
| D | 8.82 | 8.92 | 9.02 |
| D1 | 6.86 | 7.65 | - |
| E | 9.96 | 10.16 | 10.36 |
| E1 | 6.89 | 7.77 | 7.89 |
| e | 2.54BSC | | |
| H | 14.61 | 15.00 | 15.88 |
| L | 1.78 | 2.32 | 2.79 |
| L1 | 1.36 REF. | | |
| L2 | 1.50 REF. | | |
| L3 | 0.25 BSC | | |
| Q | 2.30 | 2.48 | 2.70 |

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